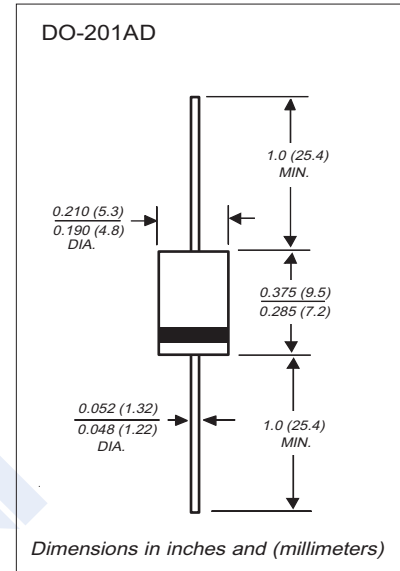


## Schottky Barrier Rectifier

### MBR320 ~ MBR3100

#### ■ Features

- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High forward surge current capability



#### ■ Absolute Maximum Ratings and Electrical Characteristics

Ratings at 25 C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbol	MBR 320	MBR 330	MBR 340	MBR 350	MBR 360	MBR 370	MBR 380	MBR 390	MBR 3100	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	20	30	40	50	60	70	80	90	100	V
Maximum RMS voltage	$V_{RMS}$	14	21	28	35	42	49	56	63	70	
Maximum DC Blocking Voltage	$V_{DC}$	20	30	40	50	60	70	80	90	100	
Maximum average forward rectified current 0.375"(9.5mm) lead length(see fig.1)	$I_{(AV)}$	3.0									A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	80.0									
Maximum instantaneous forward voltage at 3.0A	$V_F$	0.55			0.70			0.85			V
Maximum DC reverse current $T_A=25^{\circ}C$ at rated DC blocking voltage $T_A=100^{\circ}C$	$I_R$	0.5									mA
		20			10						
Typical junction capacitance (Note 1)	$C_j$	250			160						pF
Typical thermal resistance (Note 2)	$R_{thJA}$	40									$^{\circ}C/W$
Junction Temperature	$T_j$	-65 to +125			-65 to +150						$^{\circ}C$
Storage Temperature	$T_{stg}$	-65 to +150									

Notes:

1. Measured at 1MHz and applied reverse voltage of 4V D.C
2. Thermal resistance from junction to ambient at 0.375"(9.5mm)lead length,P.C.B. mounted

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### Typical Characteristics

